

Transistors

2SC9016

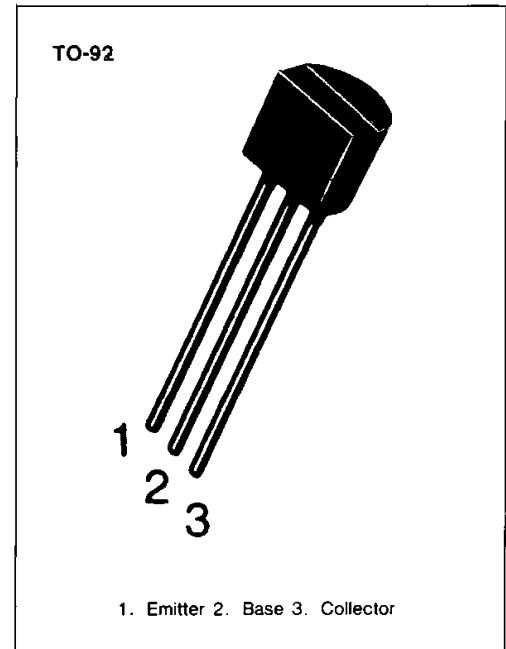


AM CONVERTER, FM/RF AMPLIFIER OF LOW NOISE.

- High total power dissipation. (PT=400mW)

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	25	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

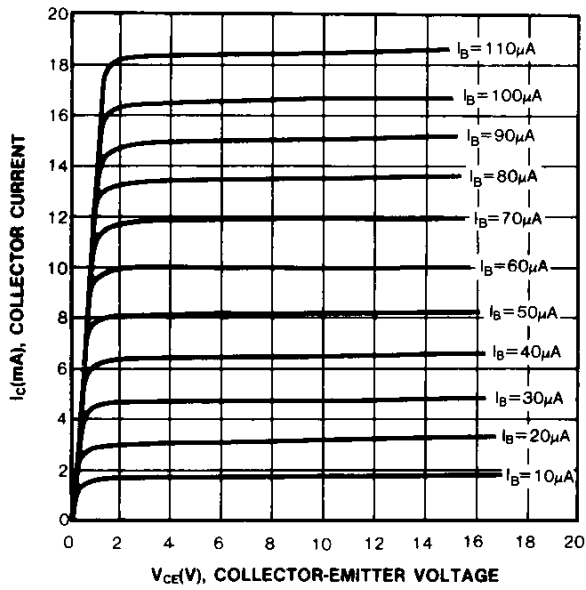
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100\mu\text{A}$, $I_E = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1\text{mA}$, $I_B = 0$	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100\mu\text{A}$, $I_C = 0$	4			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 30\text{V}$, $I_E = 0$			100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 3\text{V}$, $I_C = 0$			100	nA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 1\text{mA}$	28	90	198	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}$, $I_B = 1\text{mA}$		0.1	0.3	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = 5\text{V}$, $I_C = 1\text{mA}$		0.72		V
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$ $f = 1\text{MHz}$		1.2	1.6	pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = 5\text{V}$, $I_C = 1\text{mA}$	400	620		MHz
Noise Figure	NF	$V_{CE} = 5\text{V}$, $I_C = 1.0\text{mA}$ $f = 100\text{MHz}$, $R_s = 50\Omega$		3.0	5.0	dB

h_{FE} CLASSIFICATION

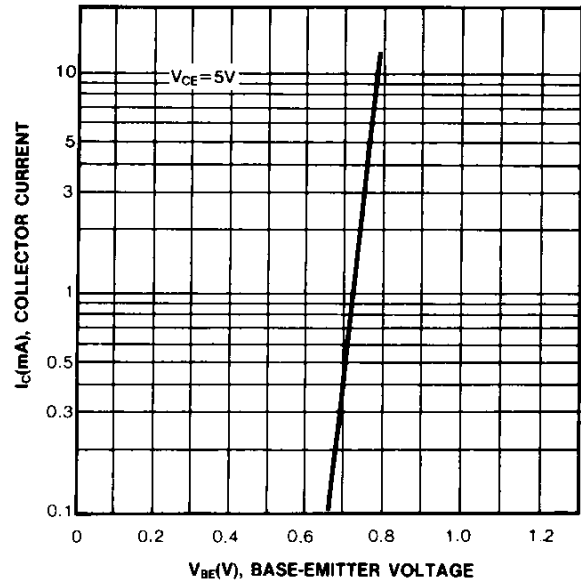
Classification	D	E	F	G	H	I
h_{FE}	28-45	39-60	54-80	72-108	97-146	132-198



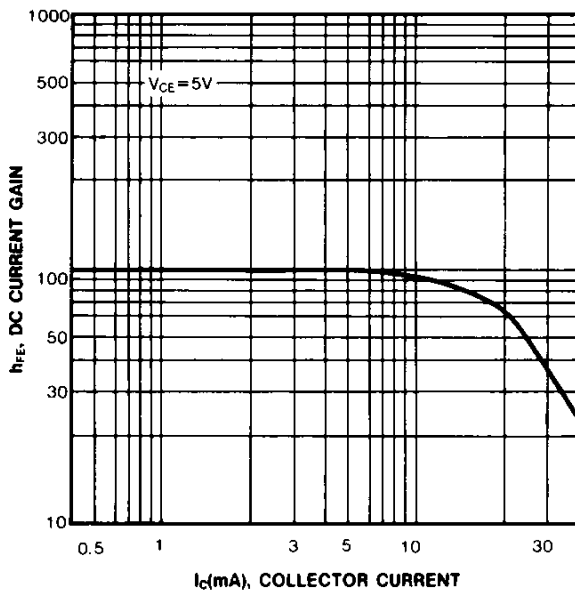
STATIC CHARACTERISTIC



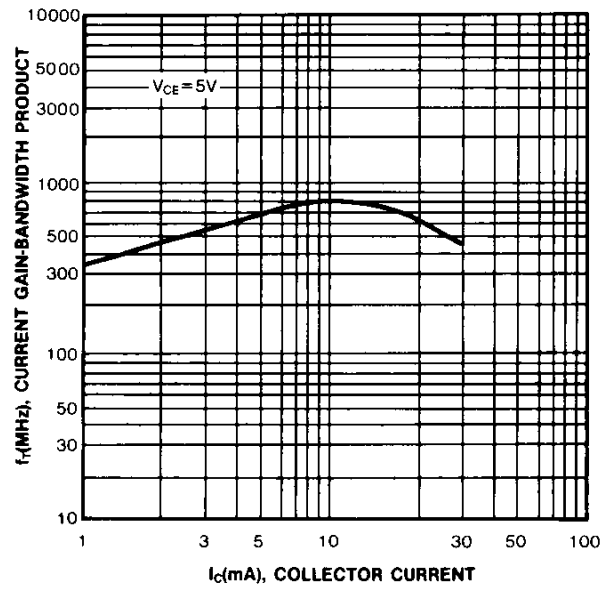
BASE-EMITTER ON VOLTAGE



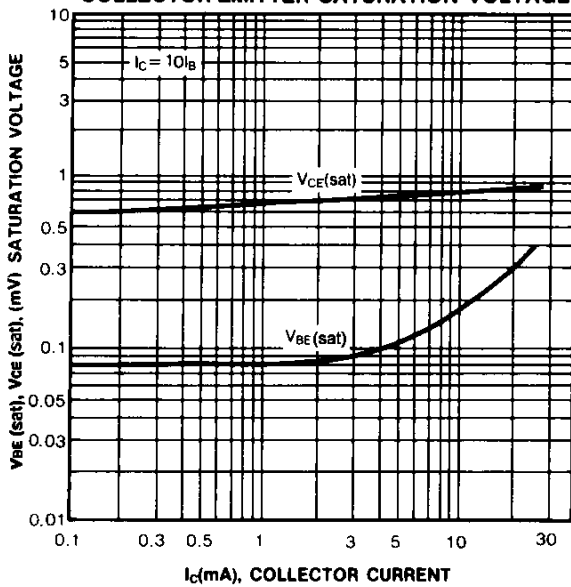
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

